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Applicant(s) Heikyung Min et al.

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n /	James Dunkley et al., "Hot Electron Induced Hydrogen Compensation of Boron Doped Silicon Resulting From Emitter-Base Breakdown", IEEE, 1992, pps. 31.4.1 – 31.4.3.												
	M. Soltani-Farshi et al., "Thermal Behaviour of Implanted Nitrogen and Accumulated Hydrogen in Titanium",												
	1998, Mat. Res. Symp. Proc. Vol. 504, Materials Research Society, pps. 231-237. O.N. Senkov and J.J. Jonas, "Dynamic Strain Aging and Hydrogen-Induced Softening in Alpha Titanium",												
V									s A, Volume 27A, July 19				
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